

## N-Channel 30-V (D-S) Fast Switching MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.0075 at $V_{GS} = 10$ V	17.8
	0.0082 at $V_{GS} = 4.5$ V	17.0

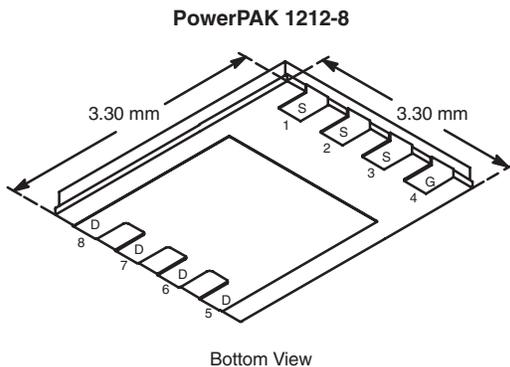
### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- New Low Thermal Resistance PowerPAK<sup>®</sup> Package with Low 1.07 mm Profile
- 100 %  $R_g$  Tested
- Lead (Pb)-free Version is RoHS Compliant



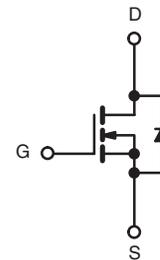
### APPLICATIONS

- Synchronous Rectification



Bottom View

Ordering Information: Si7112DN-T1  
Si7112DN-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 sec	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	30		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	17.8	11.3
		$T_A = 70$ °C	14.2	9.1
Pulsed Drain Current	$I_{DM}$	60		A
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	3.2	1.3	
Single Avalanche Current	$I_{AS}$	L = 0.1 mH	20	
Single Avalanche Energy			$E_{AS}$	20
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	3.8	1.5
		$T_A = 70$ °C	2.0	0.8
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ sec	24	33	°C/W
		Steady State	65	81	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	1.9	2.4		

Notes:

- Surface Mounted on 1" x 1" FR4 Board.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

<b>MOSFET SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.6		1.5	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
		$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	40			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 17.8\ \text{A}$		0.006	0.0075	$\Omega$
		$V_{GS} = 4.5\ \text{V}, I_D = 17\ \text{A}$		0.0065	0.0082	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\ \text{V}, I_D = 17.8\ \text{A}$		97		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 3.2\ \text{A}, V_{GS} = 0\ \text{V}$		0.7	1.2	V
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$		260		$\mu\text{F}$
Output Capacitance	$C_{oss}$			340		
Reverse Transfer Capacitance	$C_{rss}$			145		
Total Gate Charge	$Q_g$	$V_{DS} = 15\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 17.8\ \text{A}$		18	27	$\text{nC}$
Gate-Source Charge	$Q_{gs}$			6.2		
Gate-Drain Charge	$Q_{gd}$			3.1		
Gate Resistance	$R_g$	$f = 1\ \text{MHz}$	0.5	1.2	1.8	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \equiv 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_g = 6\ \Omega$		10	15	$\text{ns}$
Rise Time	$t_r$			10	15	
Turn-Off Delay Time	$t_{d(off)}$			65	100	
Fall Time	$t_f$			10	15	
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 3.2\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		30	60	$\text{ns}$
Body Diode Reverse Recovery Charge	$Q_{rr}$			18		

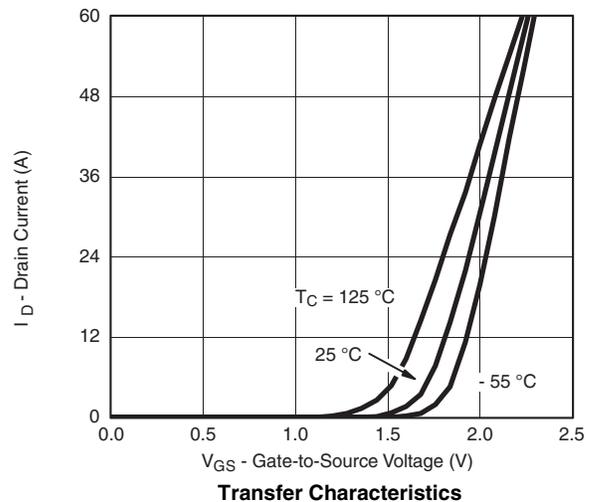
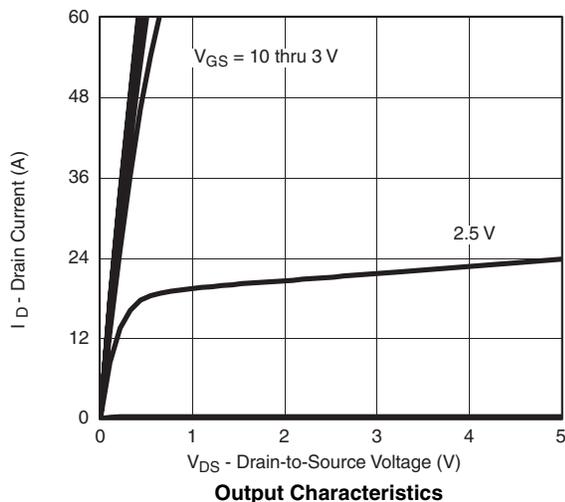
Notes:

a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

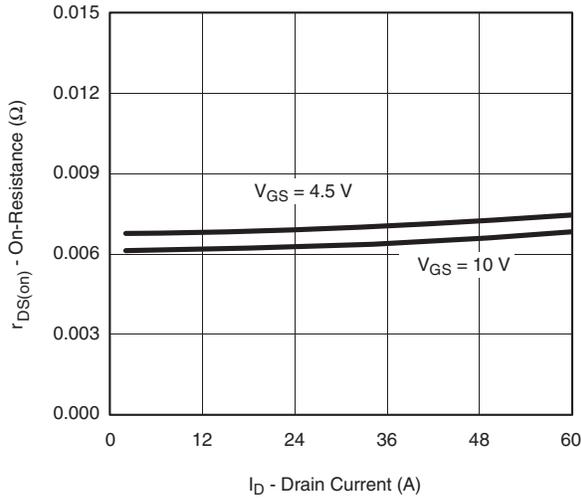
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

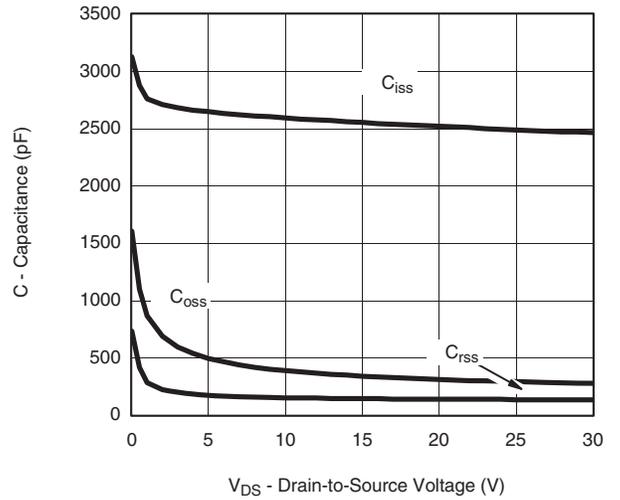
## TYPICAL CHARACTERISTICS 25 °C unless noted



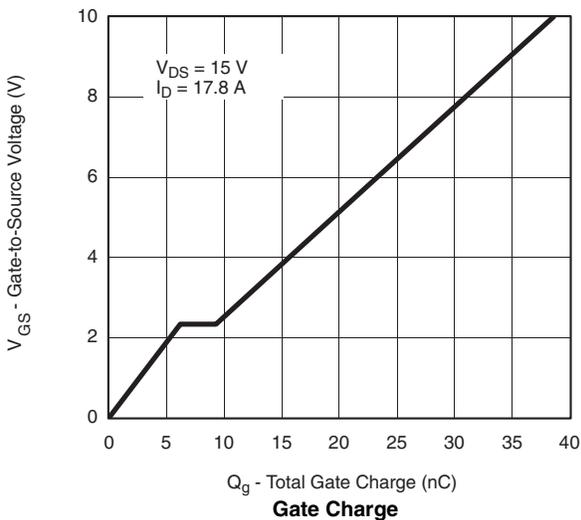
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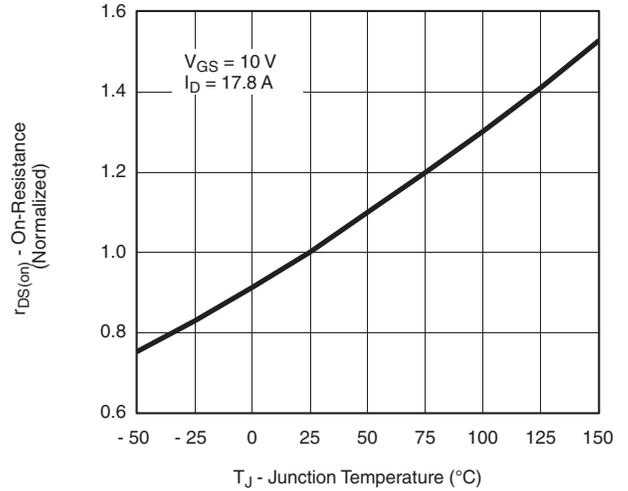
**On-Resistance vs. Drain Current**



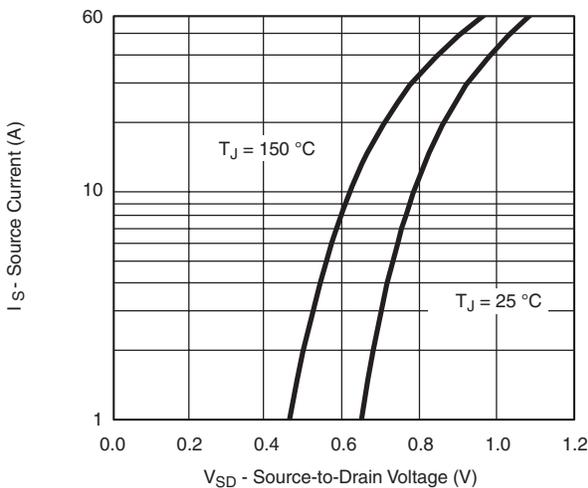
**Capacitance**



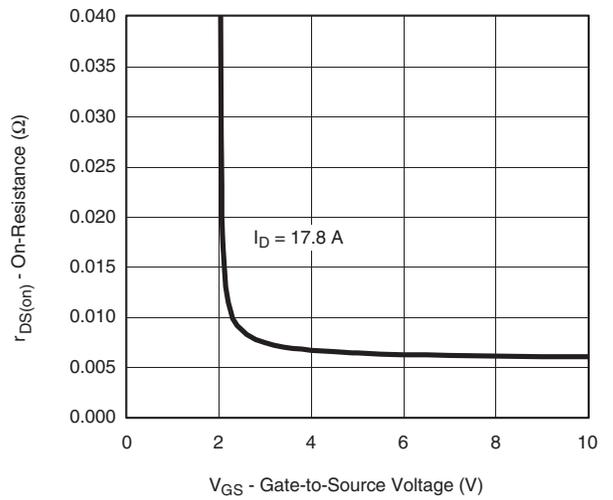
**Gate Charge**



**On-Resistance vs. Junction Temperature**

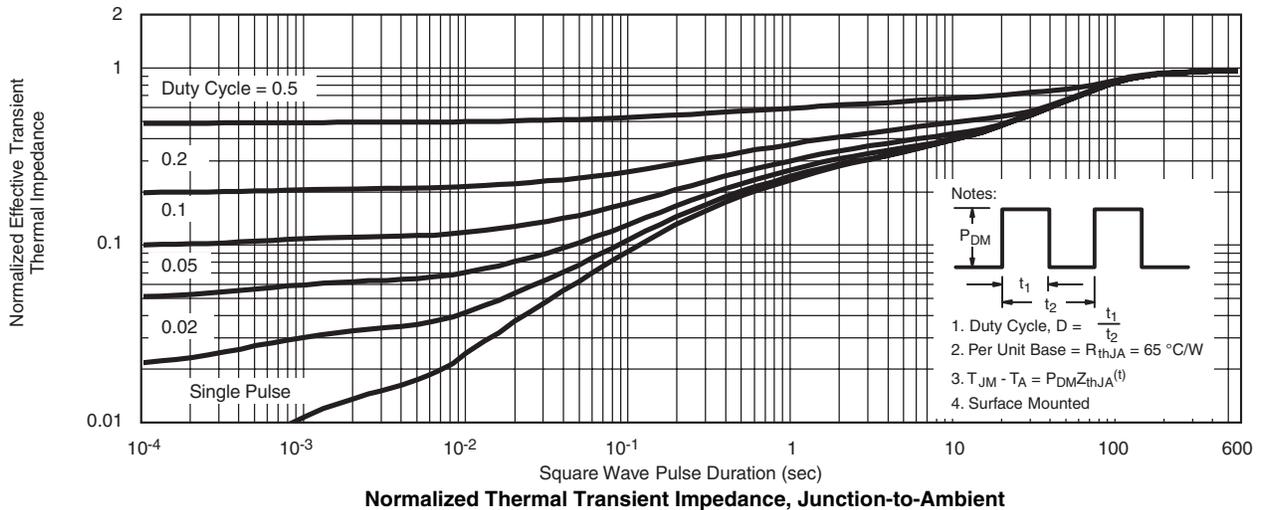
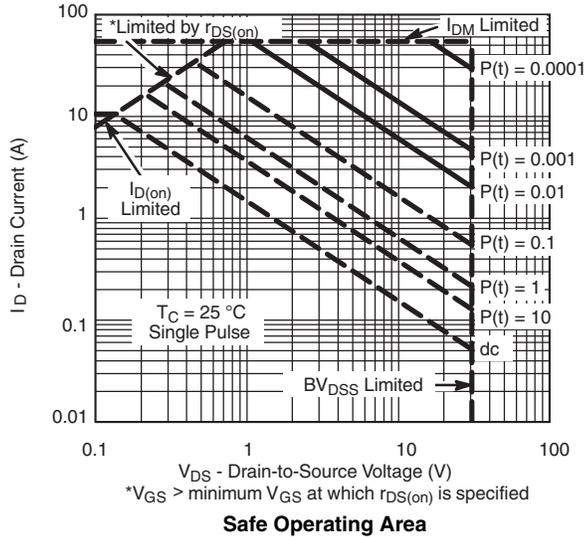
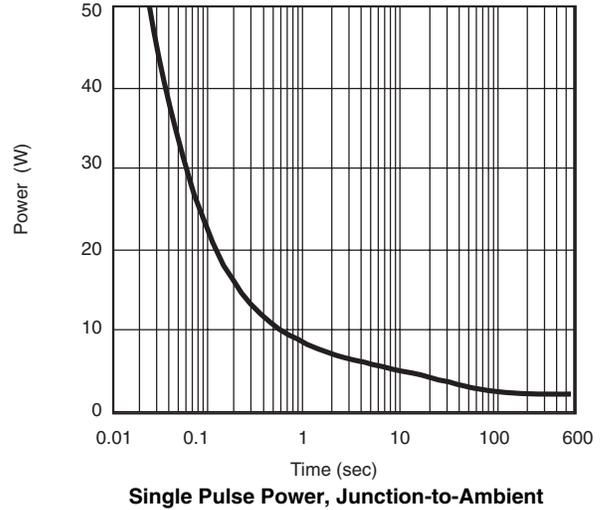
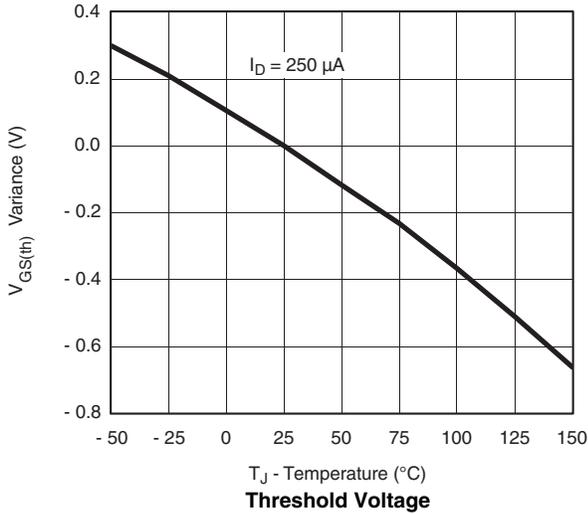


**Source-Drain Diode Forward Voltage**

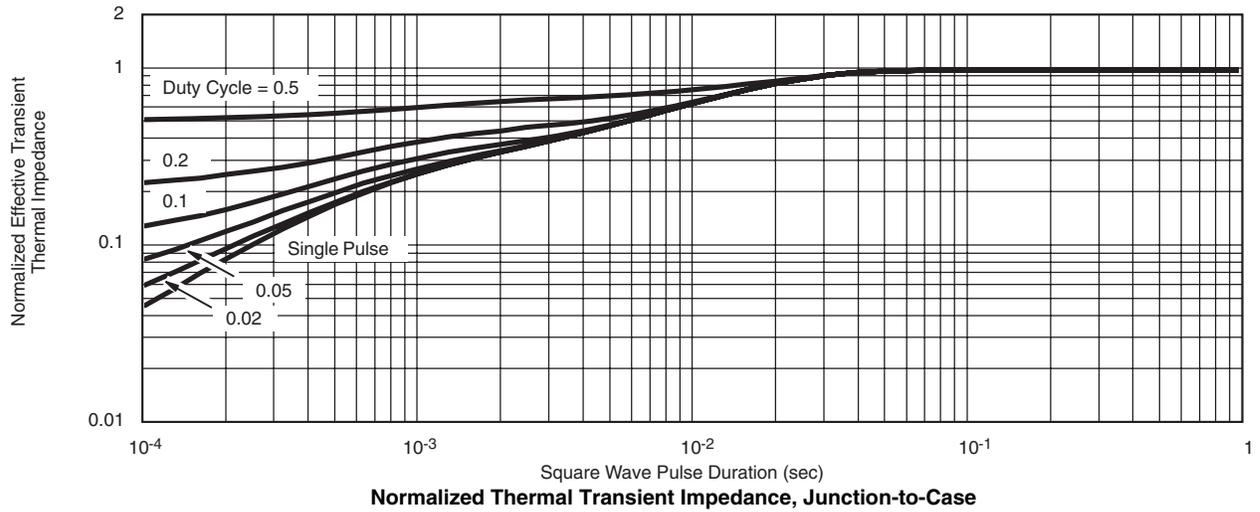


**On-Resistance vs. Gate-to-Source Voltage**

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